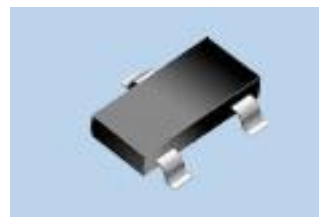


**PNP Transistors**


1.Base  
2.Emitter  
3.Collector

**Features**

- Collector current:  $I_c = 0.5A$

**Simplified outline(SOT-23)**
**Absolute Maximum Ratings  $T_a = 25^\circ C$** 

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_c$	-0.5	A
Collector Power Dissipation	$P_c$	0.3	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ C$

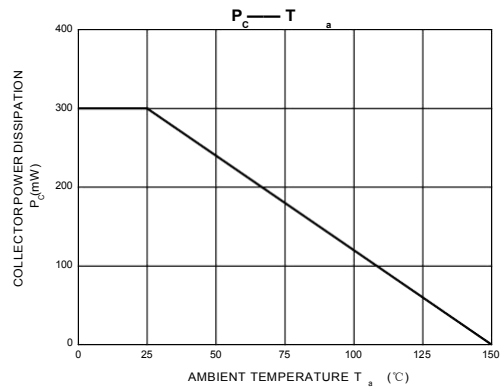
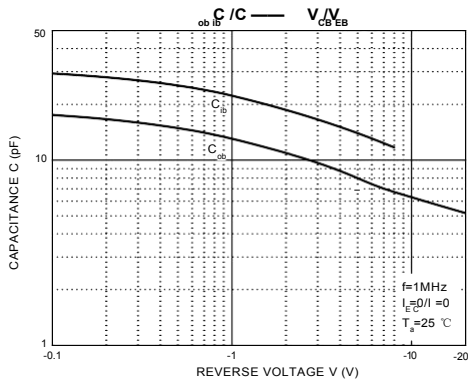
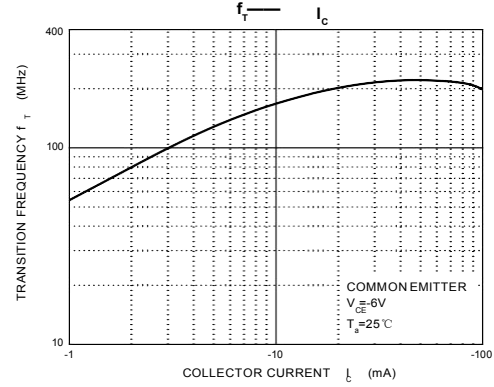
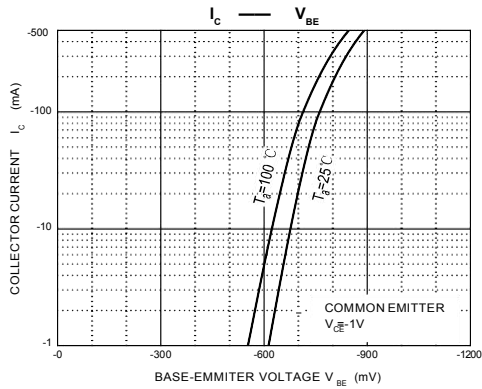
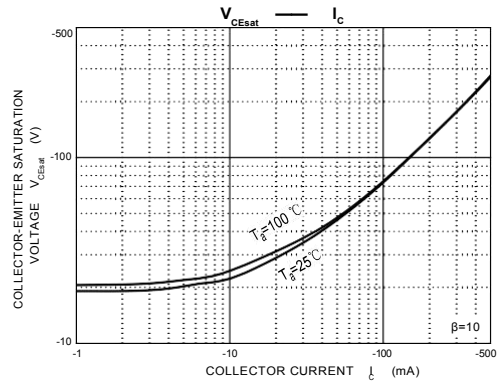
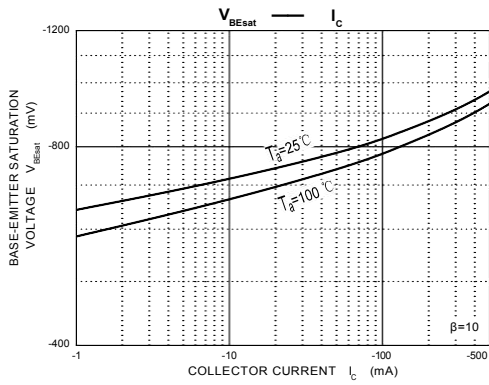
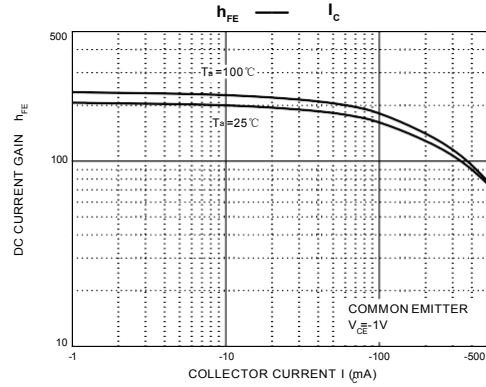
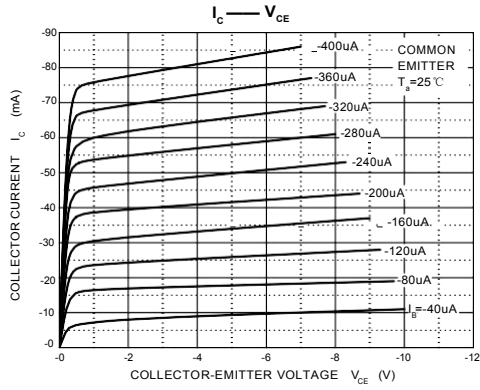
**Electrical Characteristics  $T_a = 25^\circ C$** 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_c = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_c = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -100\mu A, I_c = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -20V, I_B = 0$			-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -3V, I_c = 0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -1V, I_c = -50mA$	120		400	
		$V_{CE} = -1V, I_c = -500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -500mA, I_B = -50mA$			-1.2	V
Transition frequency	$f_T$	$V_{CE} = -6V, I_c = -20mA, f = 30MHz$	150			MHz

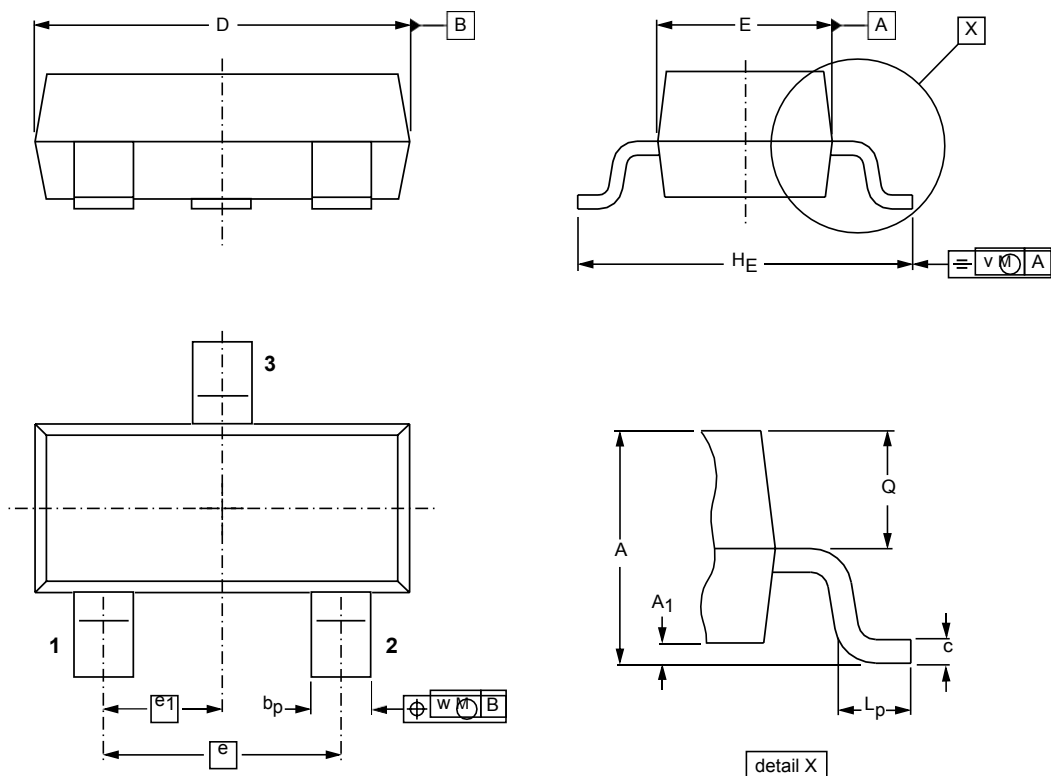
**Classification of  $h_{FE(1)}$** 

Type	S8550	S8550-L	S8550-H	S8550-J
Range	200-350	120-200	144-202	300-400
Marking	2TY			

■ Typical Characteristics



■ SOT-23



**DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1